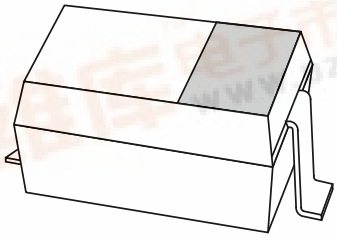
DATA SHEET



BAS316
High-speed diode

Product specification
Supersedes data of 1998 Mar 26

2004 Feb 04

High-speed diode BAS316

FEATURES

- Very small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 100 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

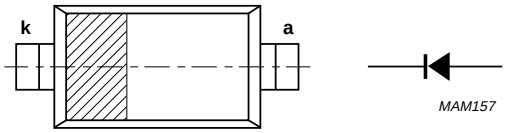
- High-speed switching in e.g. surface mounted circuits.

DESCRIPTION

The BAS316 is a high-speed switching diode fabricated in planar technology, and encapsulated in the SOD323 SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



Marking code: A6.
Cathode side indicated by a bar.

Fig.1 Simplified outline (SOD323) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BAS316	–	plastic surface mounted package; 2 leads	SOD323

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	100	V
V_R	continuous reverse voltage		–	100	V
I_F	continuous forward current	T_s = 90 °C; note 1; see Fig.2	–	250	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	–	4	A
		t = 1 ms	–	1	A
		t = 1 s	–	0.5	A
P_{tot}	total power dissipation	T_s = 90 °C; note 1	–	400	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. T_s is the temperature at the soldering point of the cathode tab.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	forward voltage	see Fig.3		
		I_F = 1 mA	715	mV
		I_F = 10 mA	855	mV
		I_F = 50 mA	1	V
		I_F = 150 mA	1.25	V
I_R	reverse current	see Fig.5		
		V_R = 25 V	30	nA
		V_R = 75 V	1	µA
		V_R = 25 V; T_j = 150 °C	30	µA
		V_R = 75 V; T_j = 150 °C	50	µA
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.6	1.5	pF
t_{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	4	ns
V_{fr}	forward recovery voltage	when switched from I_F = 10 mA; t_r = 20 ns; see Fig.8	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-s)}$	thermal resistance from junction to soldering point	note 1	150	K/W

Note

1. Soldering point of the cathode tab.

GRAPHICAL DATA

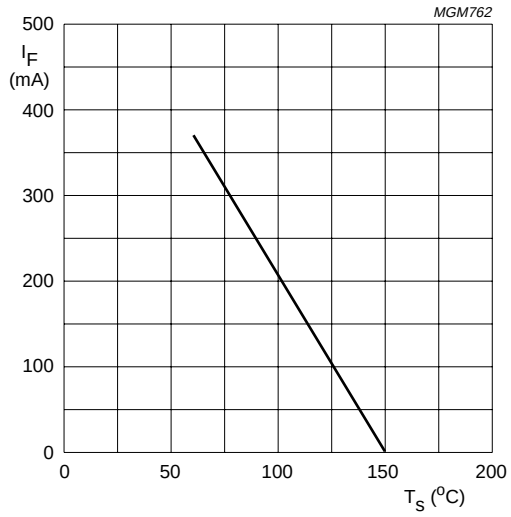
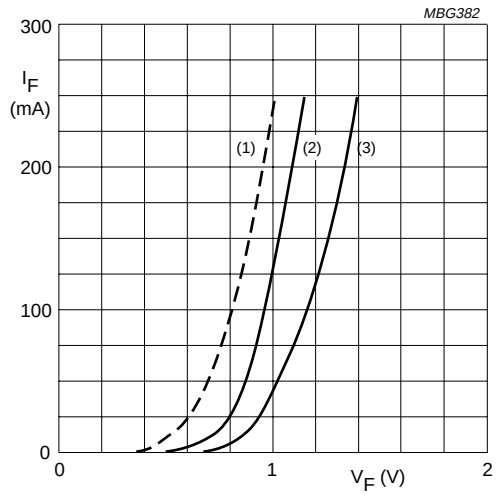
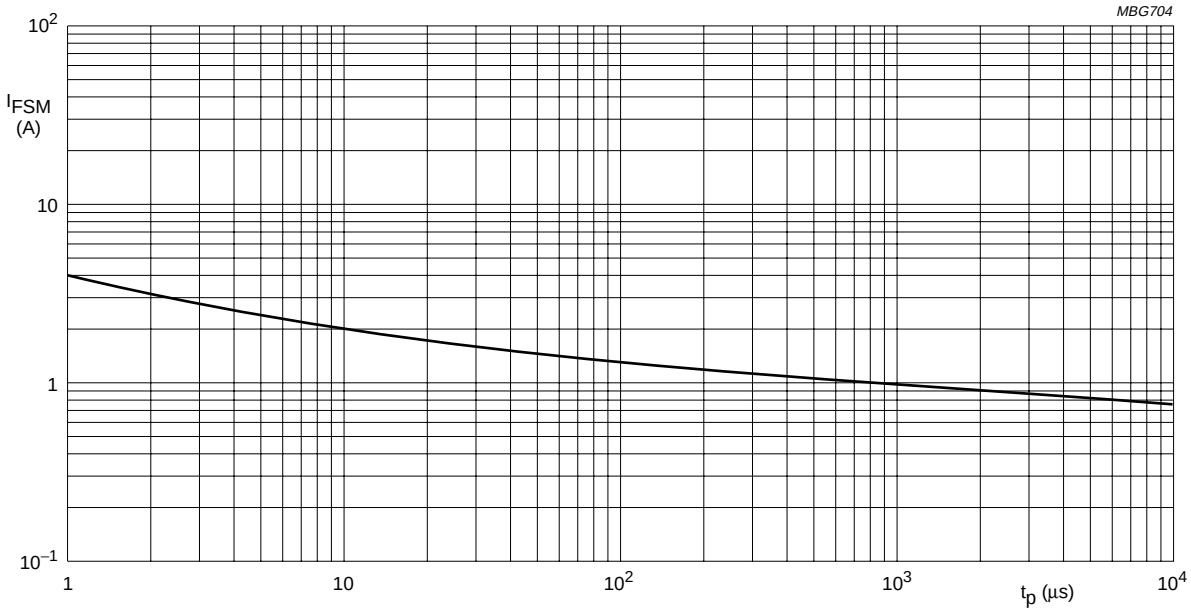


Fig.2 Maximum permissible continuous forward current as a function of soldering point temperature.



(1) T_j = 150 °C; typical values.
(2) T_j = 25 °C; typical values.
(3) T_j = 25 °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



Based on square wave currents.
T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

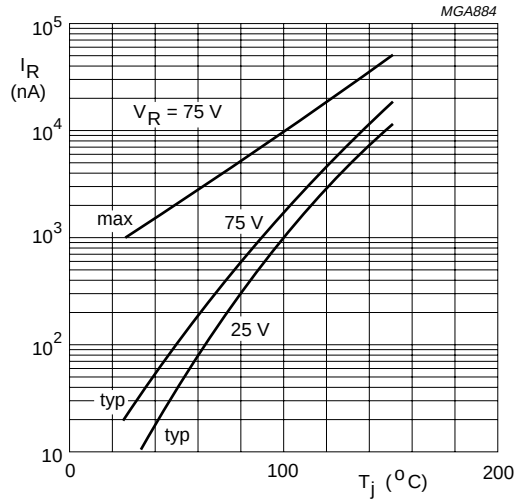
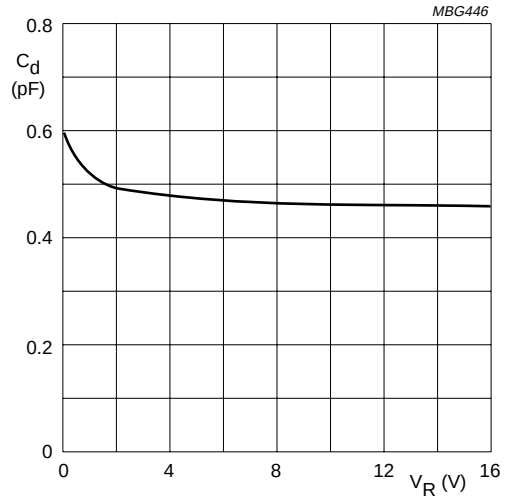
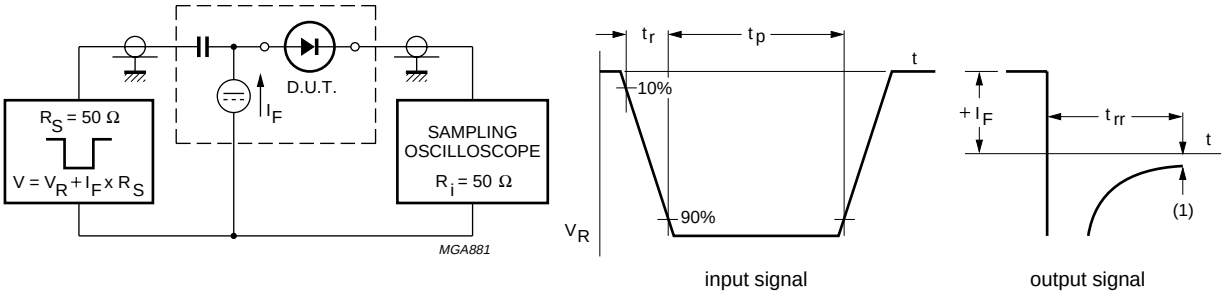


Fig.5 Reverse current as a function of junction temperature.



f = 1 MHz; T_j = 25 °C.

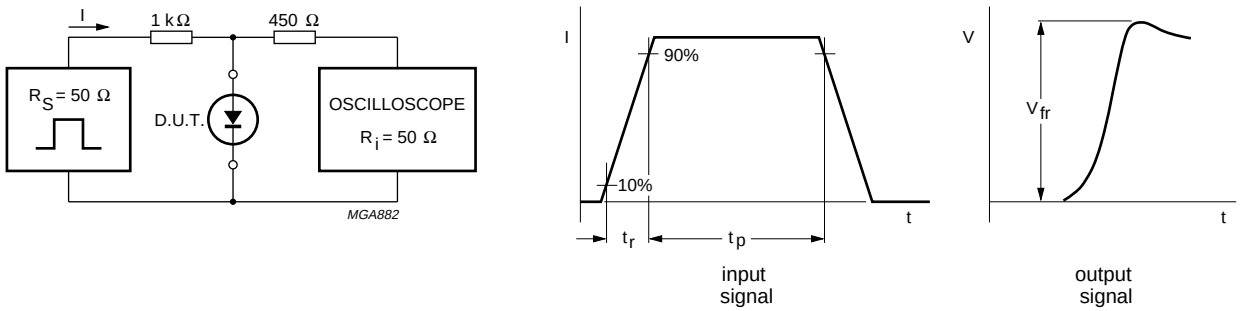
Fig.6 Diode capacitance as a function of reverse voltage; typical values.



(1) I_R = 1 mA.

Input signal: reverse pulse rise time t_r = 0.6 ns; reverse voltage pulse duration t_p = 100 ns; duty factor δ = 0.05;
Oscilloscope: rise time t_r = 0.35 ns.

Fig.7 Reverse recovery voltage test circuit and waveforms.

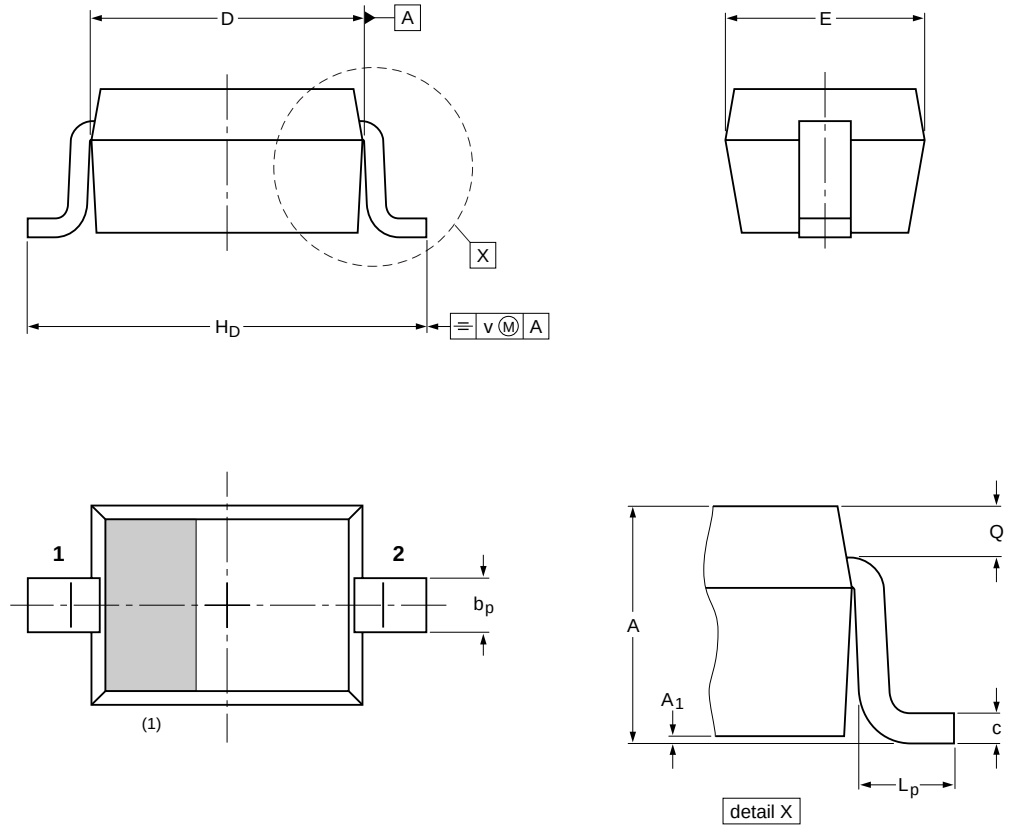


Input signal: forward pulse rise time t_r = 20 ns; forward current pulse duration $t_p \geq 100$ ns; duty factor $\delta \leq 0.005$.

Fig.8 Forward recovery voltage test circuit and waveforms.

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD323**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	H_D	L_p	Q	v
mm	1.1 0.8	0.05	0.40 0.25	0.25 0.10	1.8 1.6	1.35 1.15	2.7 2.3	0.45 0.15	0.25 0.15	0.2

Note

1. The marking bar indicates the cathode

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOD323			SC-76			~~99-09-13~~ 03-12-17

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS[1]	PRODUCT STATUS[2][3]	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Printed in The Netherlands R76/04/pp9 Date of release: 2004 Feb 04 Document order number: 9397 750 12574

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